Ordering number : ENN7607

N-Channel Silicon MOSFET

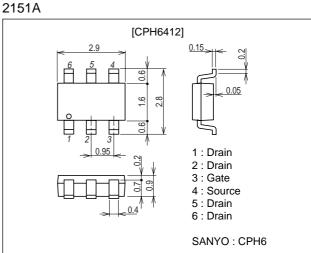


Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱D		6	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	24	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Symbol	Conditions	Ratings			Linit
		min	typ	max	Unit
V(BR)DSS	ID=1mA, VGS=0	30			V
IDSS	VDS=30V, VGS=0			1	μΑ
IGSS	V _{GS} =±16V, V _{DS} =0			±10	μΑ
V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
yfs	V _{DS} =10V, I _D =3A	4.2	6		S
R _{DS} (on)1	ID=3A, VGS=10V		25	33	mΩ
R _{DS} (on)2	ID=1.5A, VGS=4.5V		35	49	mΩ
RDS(on)3	ID=1.5A, VGS=4V		37	52	mΩ
	V(BR)DSS IDSS IGSS VGS(off) yfs RDS(on)1 RDS(on)2	V(BR)DSS ID=1mA, VGS=0 IDSS VDS=30V, VGS=0 IGSS VGS=±16V, VDS=0 VGS(off) VDS=10V, ID=1mA yfs VDS=10V, ID=3A RDS(on)1 ID=3A, VGS=10V RDS(on)2 ID=1.5A, VGS=4.5V	Min min V(BR)DSS ID=1mA, VGS=0 30 IDSS VDS=30V, VGS=0 10 IGSS VGS=16V, VDS=0 12 VGS(off) VDS=10V, ID=1mA 1.2 Iyfs VDS=10V, ID=3A 4.2 RDS(on)1 ID=3A, VGS=10V 10 RDS(on)2 ID=1.5A, VGS=4.5V 10	Symbol Conditions min typ V(BR)DSS ID=1mA, VGS=0 30 30 IDSS VDS=30V, VGS=0	Symbol Conditions min typ max V(BR)DSS ID=1mA, VGS=0 30 30 1 IDSS VDS=30V, VGS=0 1 1 1 IGSS VGS=±16V, VDS=0 1 ±10 VGS(off) VDS=10V, ID=1mA 1.2 2.6 yfs VDS=10V, ID=3A 4.2 6 RDS(on)1 ID=3A, VGS=10V 25 33 RDS(on)2 ID=1.5A, VGS=4.5V 35 49

Marking : KN

Continued on next page.

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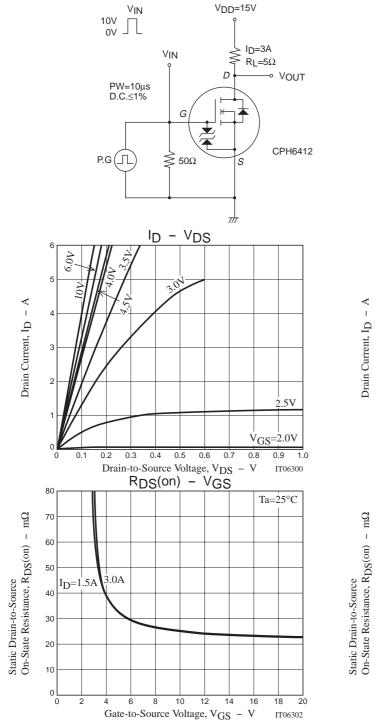
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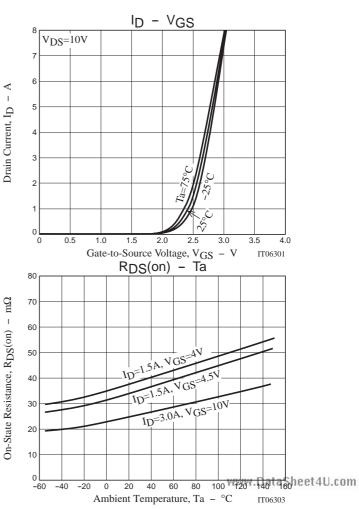
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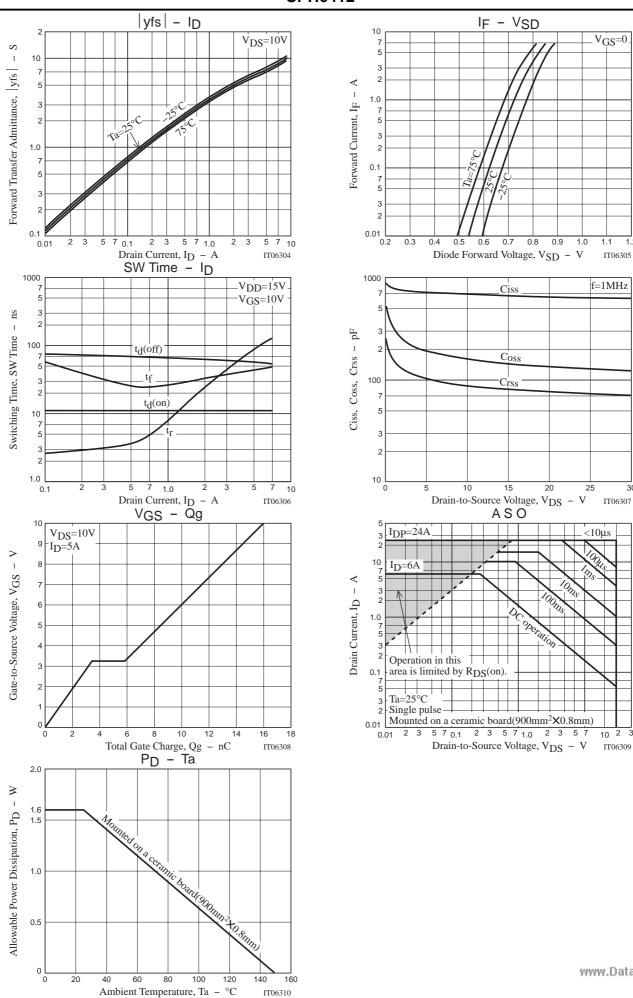
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		690		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		160		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		88		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		11		ns
Rise Time	tr	See specified Test Circuit.		45		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		60		ns
Fall Time	tf	See specified Test Circuit.		35		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =5A		16		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =5A		3.4		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =5A		2.4		nC
Diode Forward Voltage	VSD	IS=6A, VGS=0		0.84	1.2	V

Switching Time Test Circuit







CPH6412

V_{GS}=0

1.0

25

<10µs

10 2 3

30

1.1 1.2

f=1MHz

IT06305

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